

MOSFET - Power, Single N-Channel

40 V, 0.7 mΩ, 378 A

NVMFS5C404N

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFS5C404NWF – Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	40	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	$T_C = 25^\circ\text{C}$	I_D 378 A
		$T_C = 100^\circ\text{C}$	267
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	P_D 200 W
		$T_C = 100^\circ\text{C}$	100
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D 53 A
		$T_A = 100^\circ\text{C}$	37
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	P_D 3.9 W
		$T_A = 100^\circ\text{C}$	1.9
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM} 900	A
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	I_S	191	A
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 38 \text{ A}$)	E_{AS}	907	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

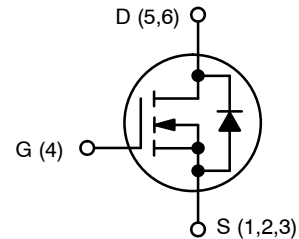
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

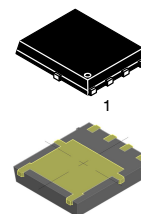
Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	0.75	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	39	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
40 V	0.7 mΩ @ 10 V	378 A



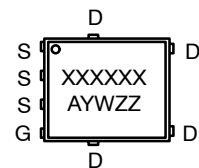
N-CHANNEL MOSFET



DFN5
CASE 506EZ

DFNW5
CASE 507BA

MARKING DIAGRAMS



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NVMFS5C404N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			19.7		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 40 V	T _J = 25 °C		10	μA
			T _J = 125°C		250	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	2.0		4.0	V
Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-6.2		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 50 A		0.57	0.7	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 50 A		210		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 25 V		8400		pF
Output Capacitance	C _{OSS}			4600		
Reverse Transfer Capacitance	C _{RSS}			120		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 20 V; I _D = 50 A		128		nC
Threshold Gate Charge	Q _{G(TH)}	V _{GS} = 10 V, V _{DS} = 20 V; I _D = 50 A		22		
Gate-to-Source Charge	Q _{GS}			35		
Gate-to-Drain Charge	Q _{GD}			26		
Plateau Voltage	V _{GP}			4.3		V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DS} = 20 V, I _D = 50 A, R _G = 2.5 Ω		16		ns
Rise Time	t _r			113		
Turn-Off Delay Time	t _{d(OFF)}			77		
Fall Time	t _f			109		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 50 A	T _J = 25°C		0.76	1.2	V
			T _J = 125°C		0.63		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 50 A		96		ns	
Charge Time	t _a			49			
Discharge Time	t _b			47			
Reverse Recovery Charge	Q _{RR}			189			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

NVMFS5C404N

TYPICAL CHARACTERISTICS

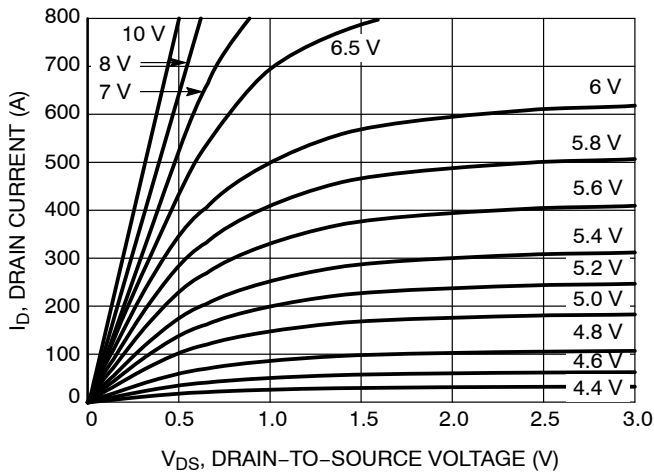


Figure 1. On-Region Characteristics

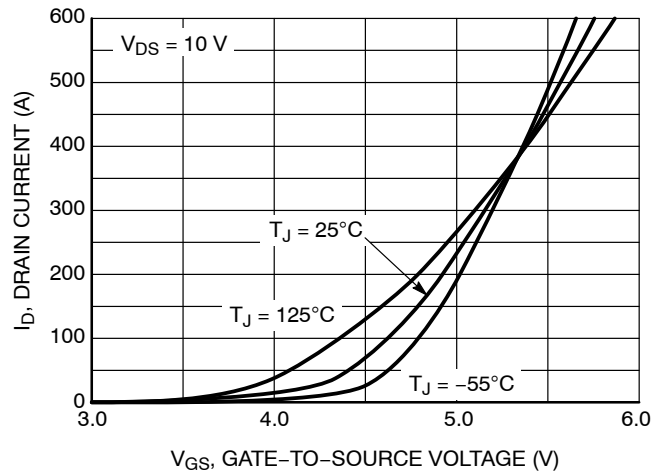


Figure 2. Transfer Characteristics

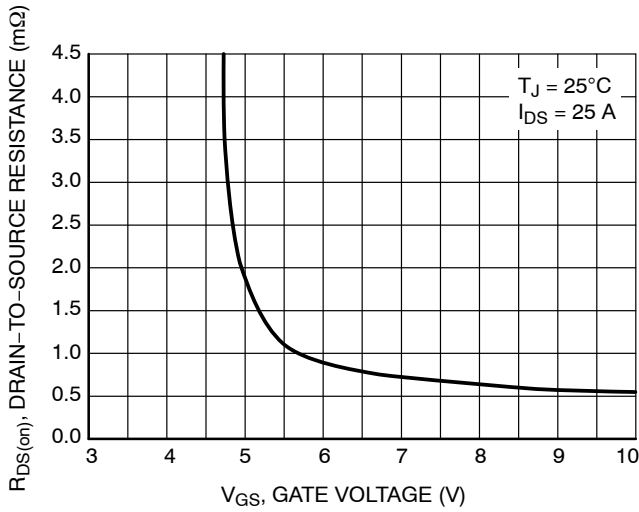


Figure 3. On-Resistance vs. Gate-to-Source Voltage

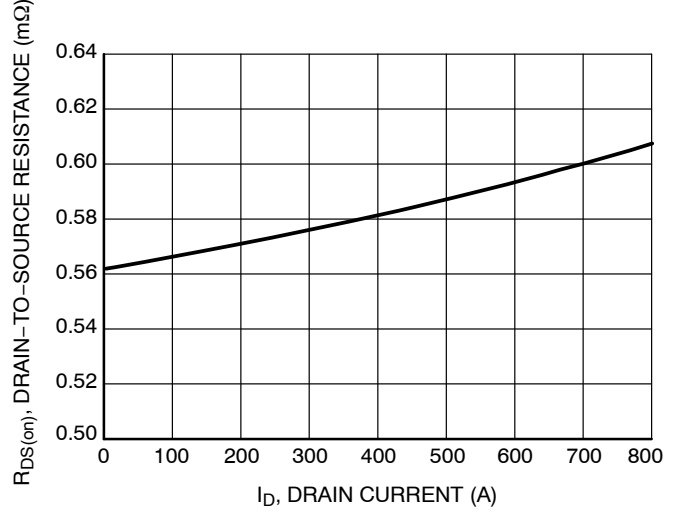


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

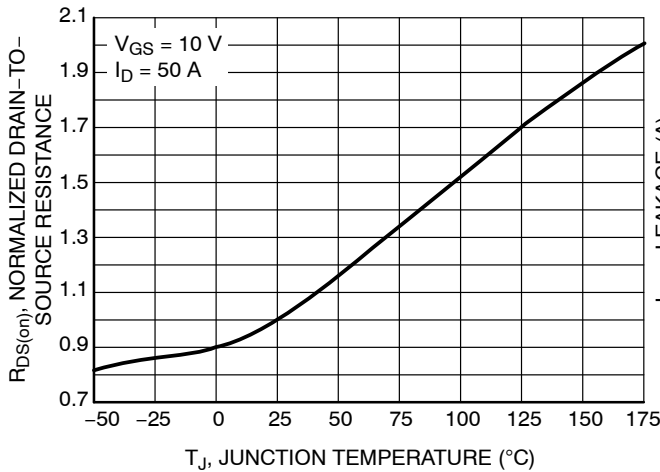


Figure 5. On-Resistance Variation with Temperature

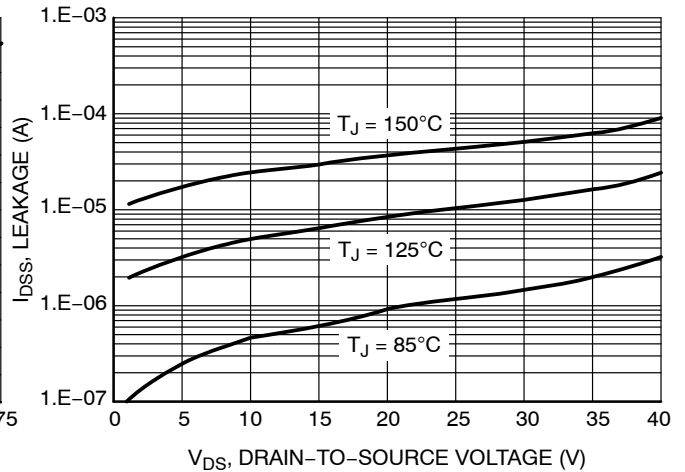


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NVMFS5C404N

TYPICAL CHARACTERISTICS

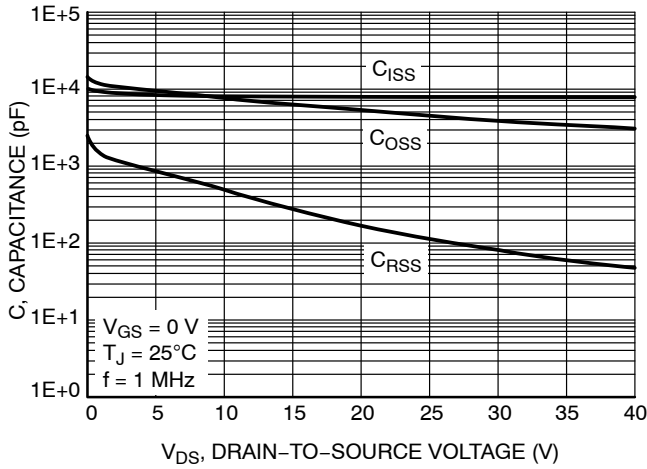


Figure 7. Capacitance Variation

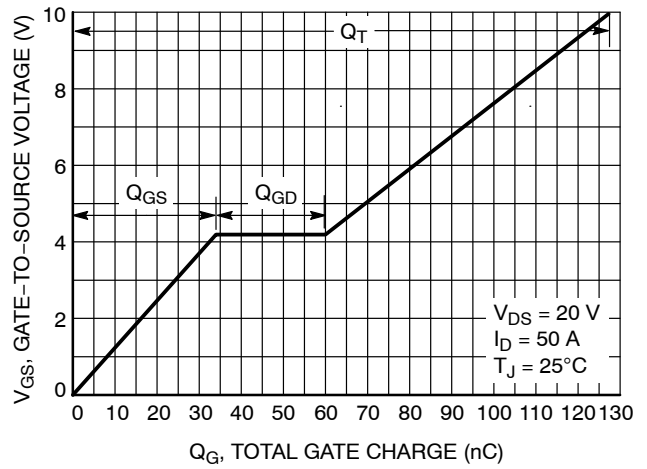


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

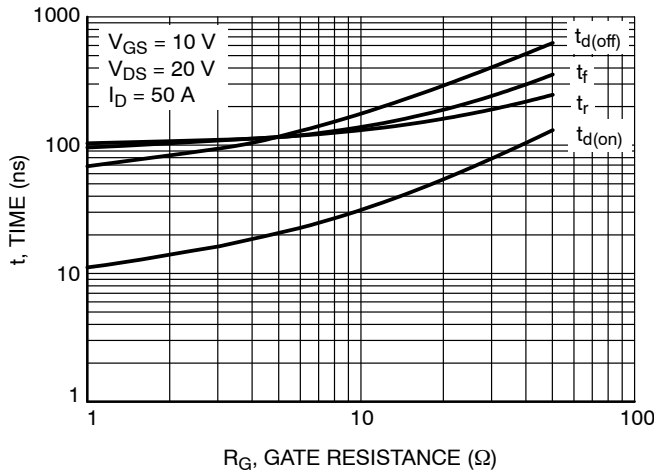


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

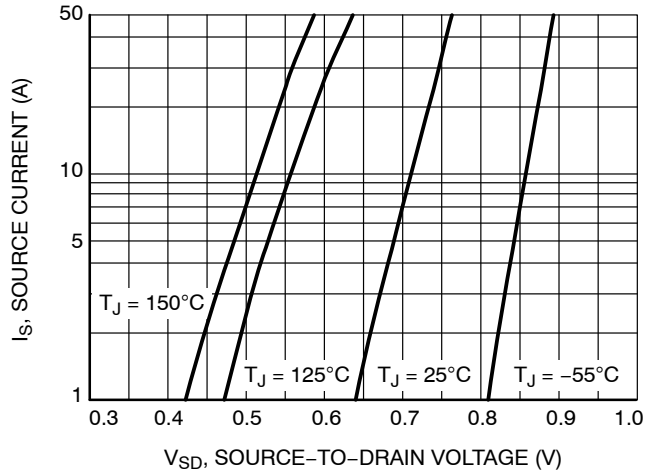


Figure 10. Diode Forward Voltage vs. Current

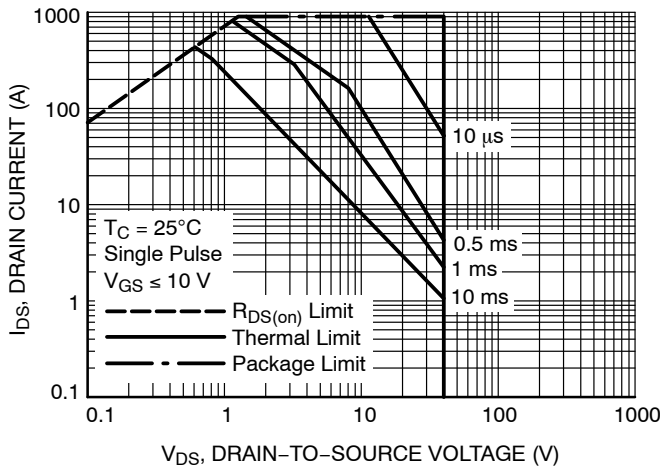


Figure 11. Maximum Rated Forward Biased Safe Operating Area

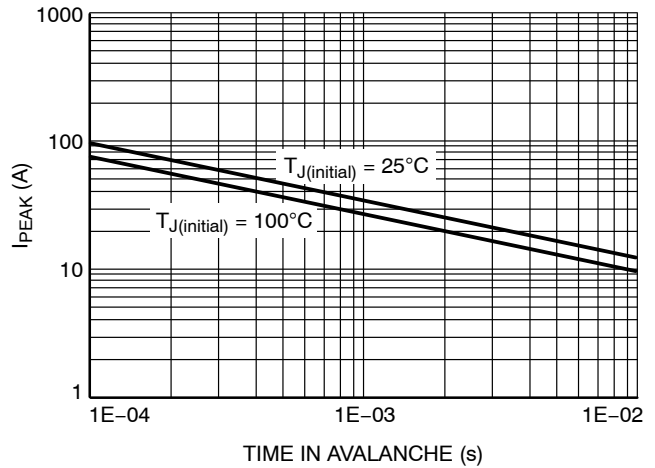


Figure 12. I_{PEAK} vs. Time in Avalanche

NVMFS5C404N

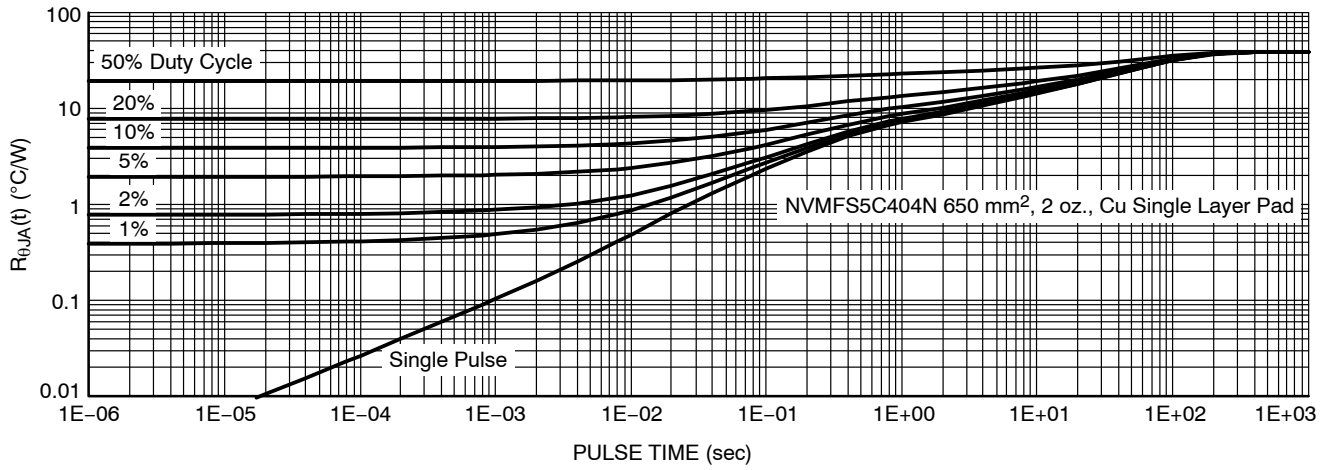


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

Device	Case	Marking	Package	Shipping [†]
NVMFS5C404NT1G	506EZ	5C404N	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C404NWFT1G	507BA	404NWF	DFNW5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C404NT3G	506EZ	5C404N	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS5C404NWFT3G	507BA	404NWF	DFNW5 (Pb-Free)	5000 / Tape & Reel
NVMFS5C404NAFT1G	506EZ	5C404N	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C404NWFAFT1G	507BA	404NWF	DFNW5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C404NWFET1G	507BA	404NWF	DFNW5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C404NWFET3G	507BA	404NWF	DFNW5 (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



1
SCALE 2:1

DFN5 5x6, 1.27P (SO-8FL)
CASE 506EZ
ISSUE A

DATE 25 AUG 2021



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.80	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
k	1.10	1.20	1.40
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 W = Work Week
 ZZ = Lot Traceability

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



DFNW5 5x6 (FULL-CUT SO8FL WF)

CASE 507BA

ISSUE A

DATE 03 FEB 2021



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.150 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
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- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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